



STB95NF03

N-CHANNEL 30V - 0.0065 Ω - 95A D²PAK
STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB95NF03	30 V	<0.007 Ω	80 A

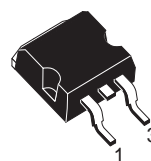
- TYPICAL R_{DS(on)} = 0.0065 Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED
- SURFACE-MOUNTING D²PAK (TO-263)
POWER PACKAGE IN TUBE (NO SUFFIX) OR
IN TAPE & REEL (SUFFIX "T4")

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

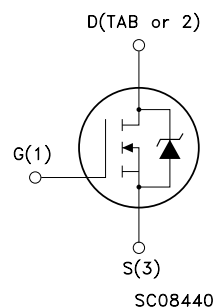
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- DC-DC & DC-AC CONVERTERS
- SOLENOID AND RELAY DRIVERS



**D²PAK
TO-263**
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	30	V
V _{GS}	Gate- source Voltage	± 20	V
I _D (*)	Drain Current (continuous) at T _C = 25°C	80	A
I _D	Drain Current (continuous) at T _C = 100°C	80	A
I _{DM} (•)	Drain Current (pulsed)	320	A
P _{tot}	Total Dissipation at T _C = 25°C	150	W
	Derating Factor	1	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3.0	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	720	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

(•) Pulse width limited by safe operating area.

(*) Current Limited by Package

(1) I_{SD} \leq 95A, di/dt \leq 150A/ μ s, V_{DD} \leq V(BR)DSS, T_j \leq T_{JMAX}.

(2) Starting T_j = 25 °C, I_D = 47.5A, V_{DD} = 25V

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _(BR) DSS	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 45 A		0.0065	0.0070	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 45 A		50		S
C _{iss}	Input Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		2450		pF
C _{oss}	Output Capacitance			880		pF
C _{rss}	Reverse Transfer Capacitance			170		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 47.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		20 195		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=15\text{ V}$ $I_D=95\text{ A}$ $V_{GS}=10\text{ V}$		59 18 21	70	nC nC nC

SWITCHING OFF(*)

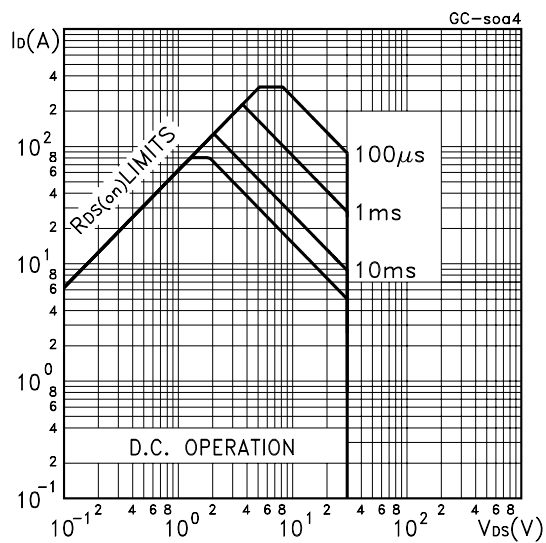
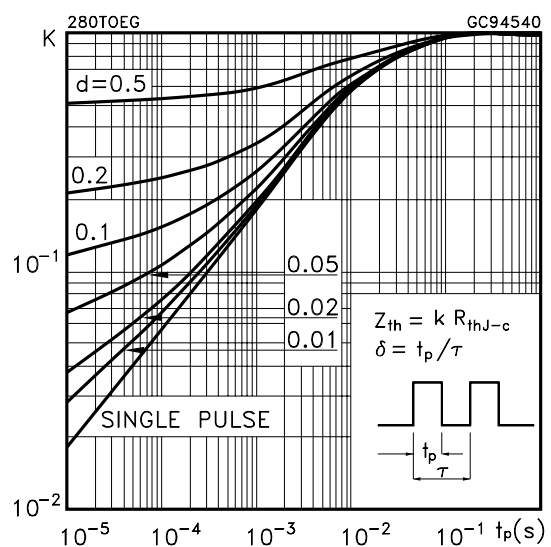
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 20\text{ V}$ $I_D = 47.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		35 35		ns ns

SOURCE DRAIN DIODE(*)

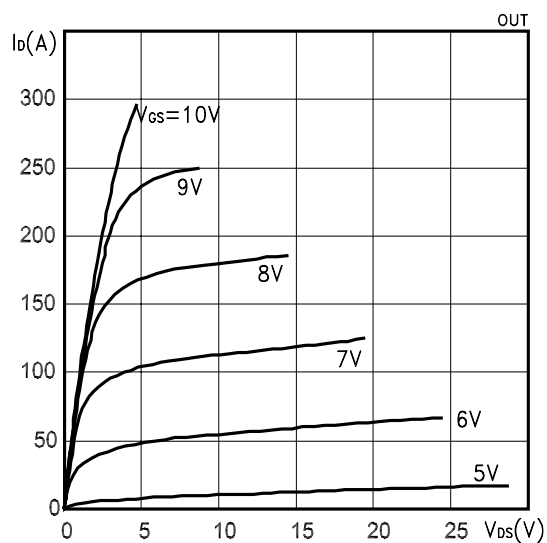
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (*)$	Source-drain Current Source-drain Current (pulsed)				95 320	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 95\text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 95\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		60 120 4		ns nC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

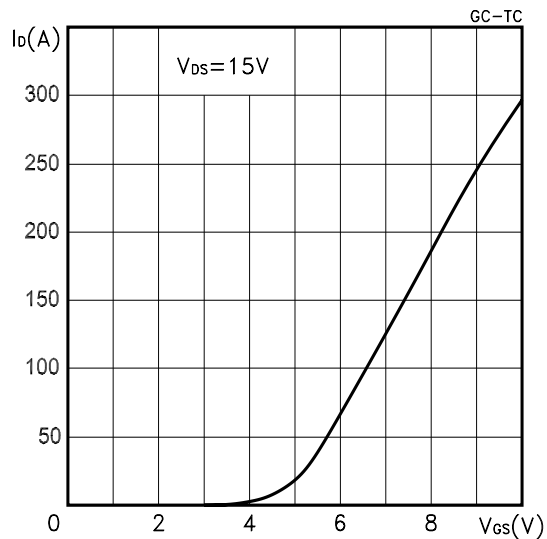
(*) Pulse width limited by T_{jmax}

Safe Operating Area

Thermal Impedance


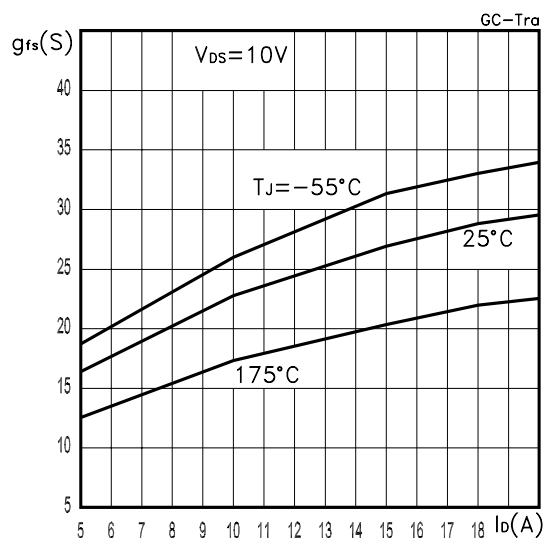
Output Characteristics



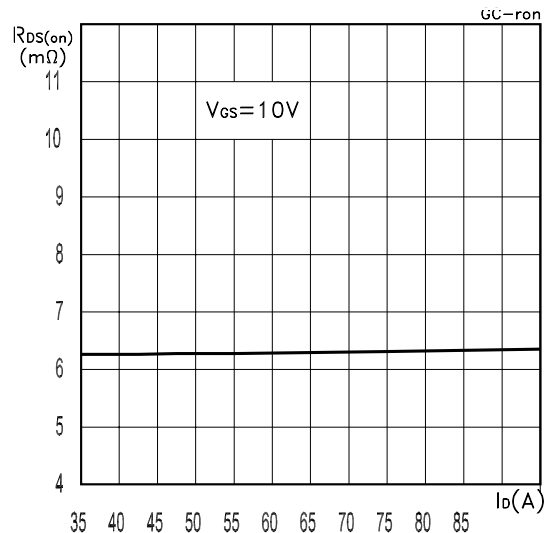
Transfer Characteristics



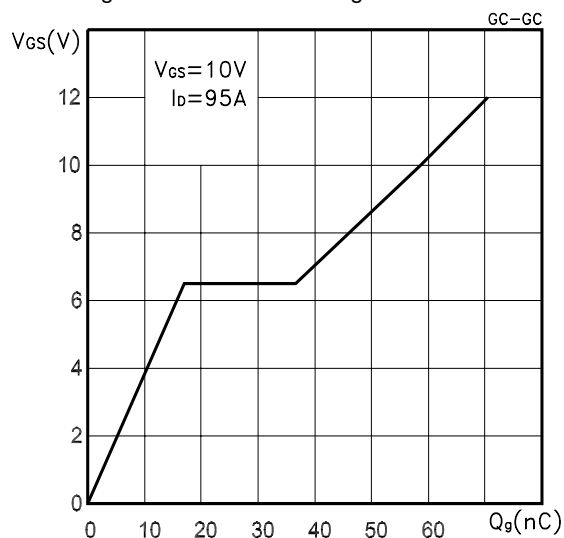
Transconductance



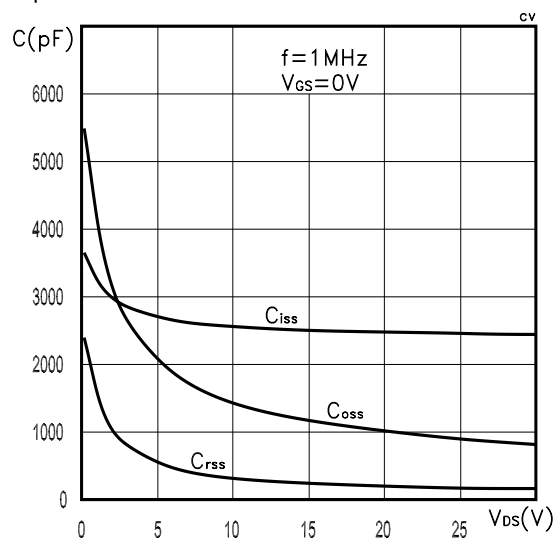
Static Drain-source On Resistance



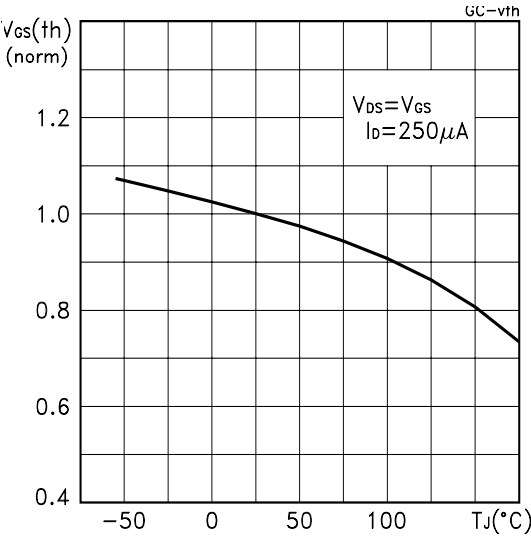
Gate Charge vs Gate-source Voltage



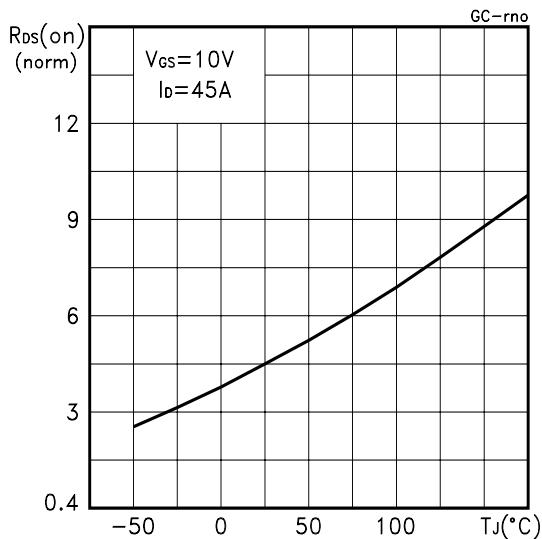
Capacitance Variations



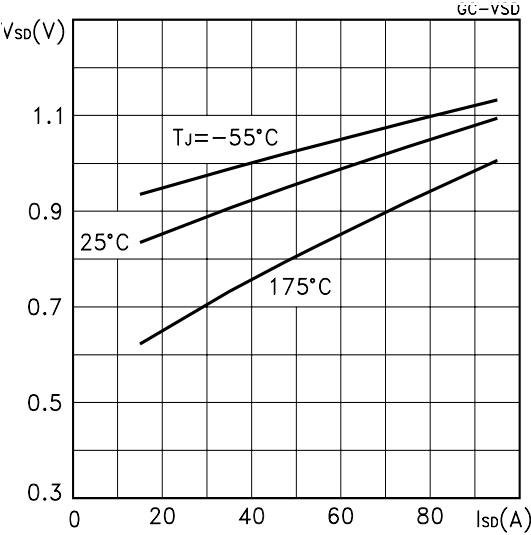
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

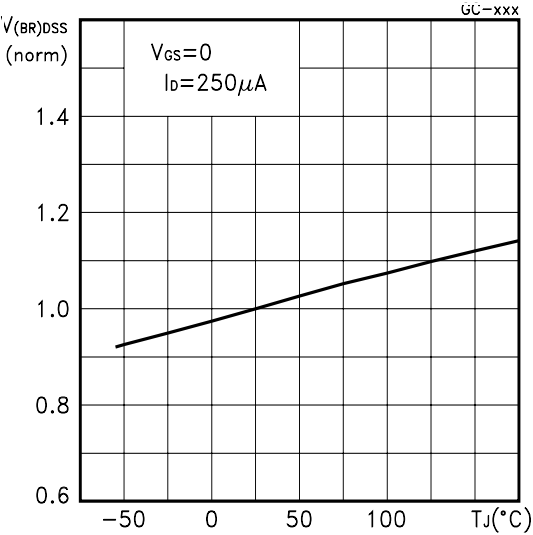
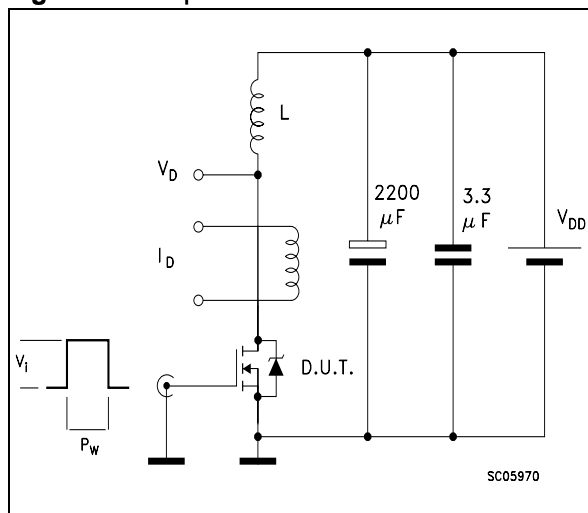
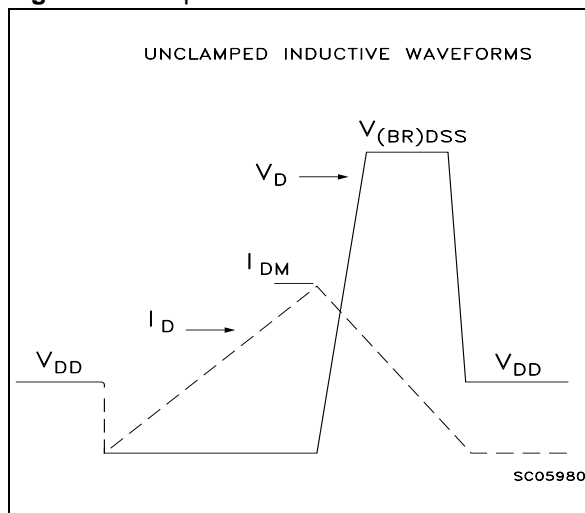
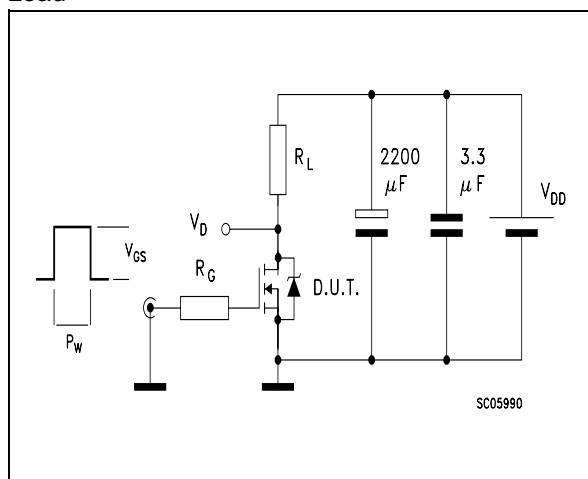
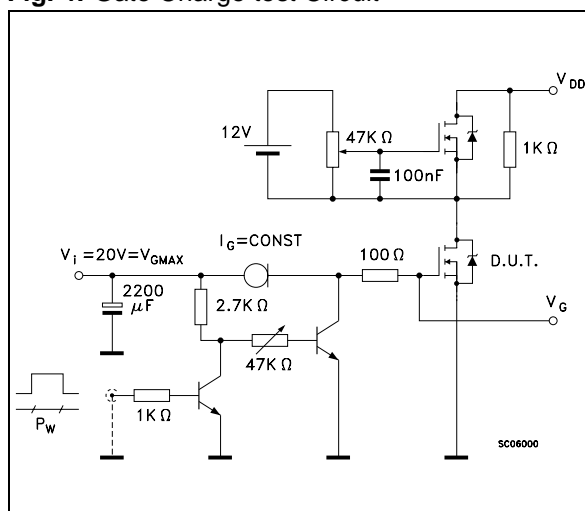
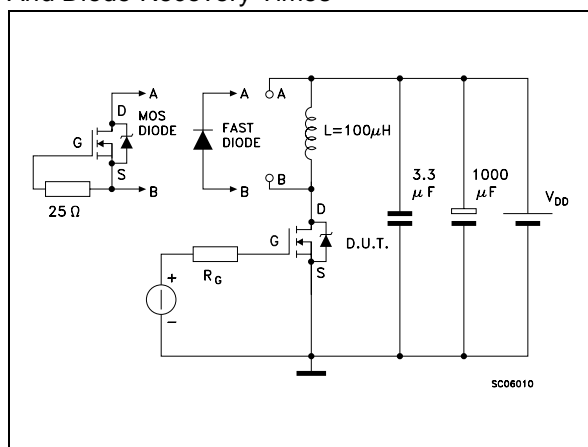
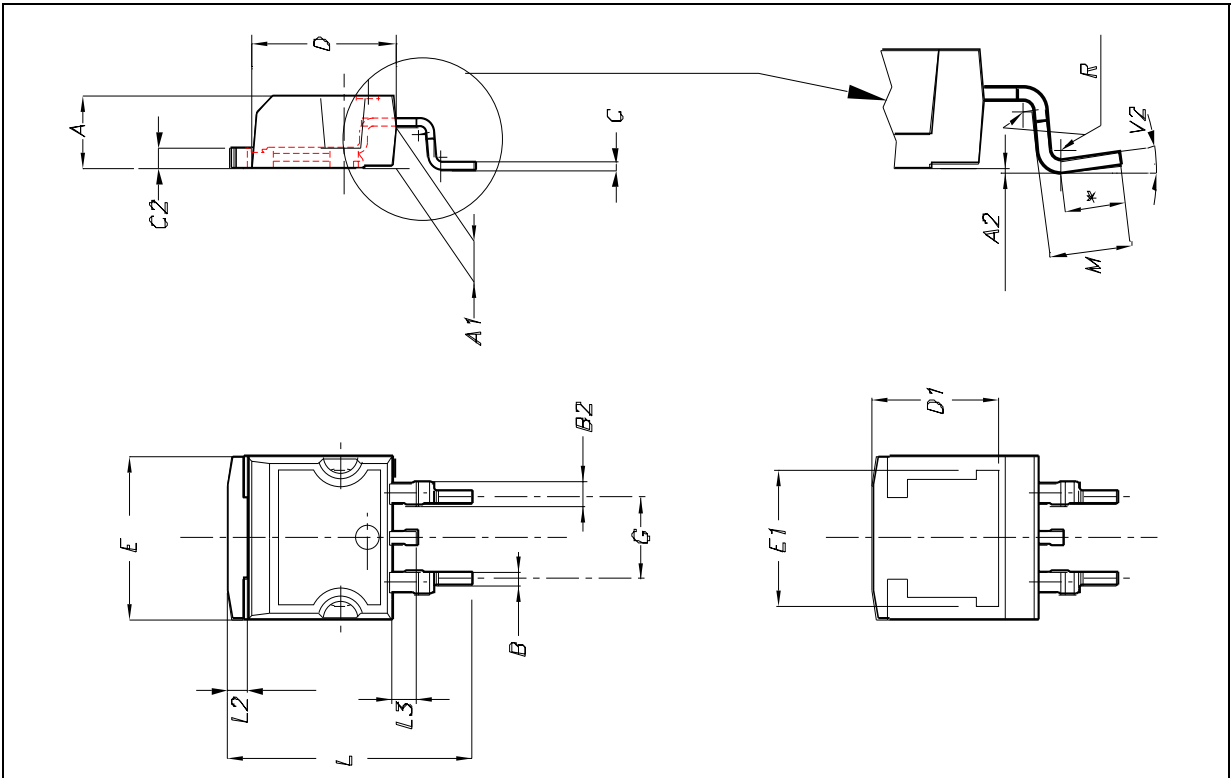


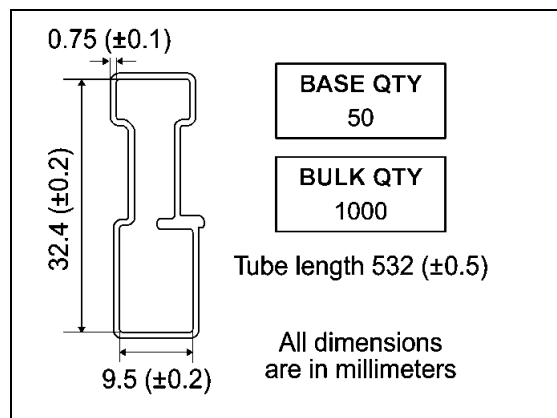
Fig. 1: Unclamped Inductive Load Test Circuit**Fig. 2: Unclamped Inductive Waveform****Fig. 3: Switching Times Test Circuits For Resistive Load****Fig. 4: Gate Charge test Circuit****Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**

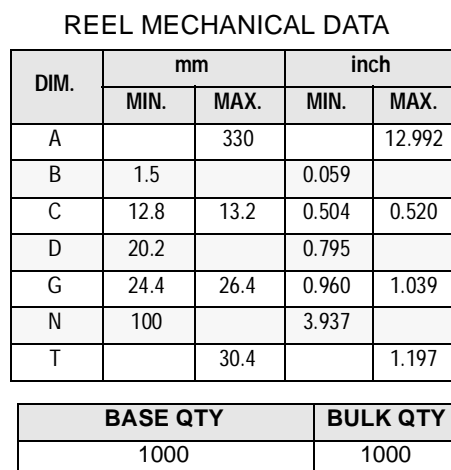
D²PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°	0°		8°

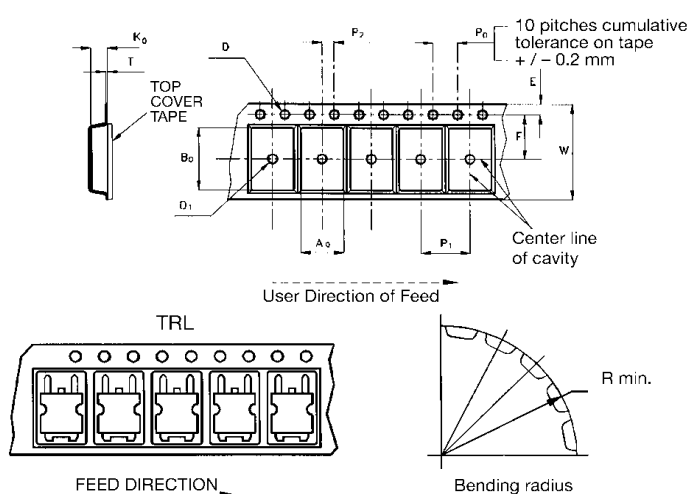


TUBE SHIPMENT (no suffix)*





DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



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